

EH25 00

Series -RoHS Compliant (Pb-free) 5.0V 4 Pad 5mm x 7mm Ceramic SMD HCMOS/TTL High Frequency Oscillator Frequency Tolerance/Stability ±100ppm Maximum

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TS -12.000M L Nominal Frequency

12.000MHz - Pin 1 Connection

Tri-State (High Impedance) Duty Cycle 50 ±10(%)

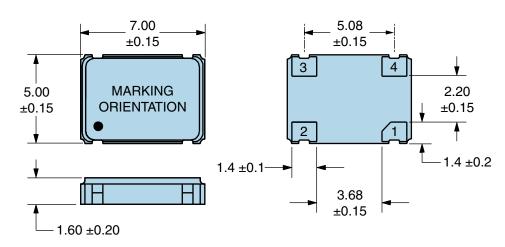
| 0°C to +70°C | 50 |
|--------------|----|
| TIONO | |

| Nominal Frequency | 12.000MHz | |
|---------------------------------------|---|--|
| Frequency Tolerance/Stability | ±100ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration) | |
| Aging at 25°C | ±5ppm/year Maximum | |
| Operating Temperature Range | 0°C to +70°C | |
| Supply Voltage | 5.0Vdc ±10% | |
| Input Current | 50mA Maximum (No Load) | |
| Output Voltage Logic High (Voh) | 2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA) | |
| Output Voltage Logic Low (Vol) | 0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA) | |
| Rise/Fall Time | 6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load) | |
| Duty Cycle | 50 ±10(%) (Measured at 1.4Vdc with TTL Load; Measured at 50% of waveform with HCMOS Load) | |
| Load Drive Capability | 10TTL Load or 50pF HCMOS Load Maximum | |
| Output Logic Type | CMOS | |
| Pin 1 Connection | Tri-State (High Impedance) | |
| Tri-State Input Voltage (Vih and Vil) | +2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output. | |
| Absolute Clock Jitter | ±250pSec Maximum, ±100pSec Typical | |
| One Sigma Clock Period Jitter | ±50pSec Maximum, ±30pSec Typical | |
| Start Up Time | 10mSec Maximum | |
| Storage Temperature Range | -55°C to +125°C | |

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

| MIL-STD-883, Method 3015, Class 1, HBM: 1500V | |
|---|--|
| MIL-STD-883, Method 1014, Condition A | |
| UL94-V0 | |
| MIL-STD-883, Method 1014, Condition C | |
| MIL-STD-883, Method 2002, Condition B | |
| MIL-STD-883, Method 1004 | |
| J-STD-020, MSL 1 | |
| MIL-STD-202, Method 210, Condition K | |
| MIL-STD-202, Method 215 | |
| MIL-STD-883, Method 2003 | |
| MIL-STD-883, Method 1010, Condition B | |
| MIL-STD-883, Method 2007, Condition A | |
| | |

MECHANICAL DIMENSIONS (all dimensions in millimeters)



| | CORPORATION |
|-----|-------------|
| | |
| PIN | CONNECTION |
| 1 | Tri-State |

IDTCI/®

| 1 | Tri-State |
|------|----------------|
| 2 | Ground |
| 3 | Output |
| 4 | Supply Voltage |
| LINE | MARKING |
| | MARAING |
| 1 | ECLIPTEK |
| 2 | 12.000M |
| | |

Suggested Solder Pad Layout

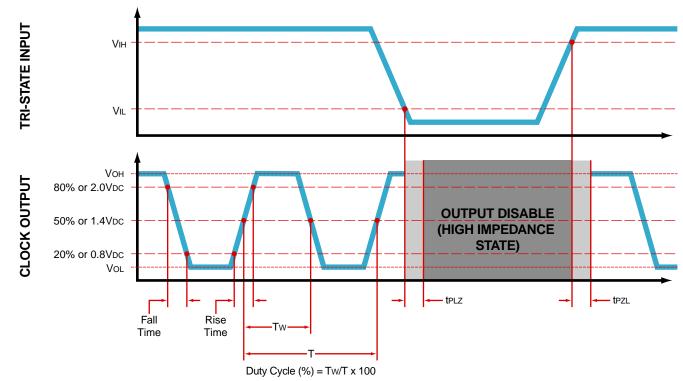
All Dimensions in Millimeters



All Tolerances are ±0.1



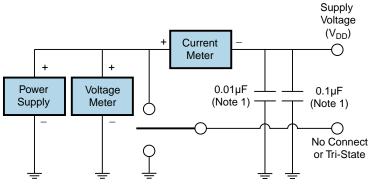
OUTPUT WAVEFORM & TIMING DIAGRAM

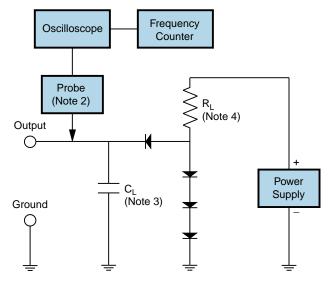


Test Circuit for TTL Output

| Output Load Drive Capability | R _L Value (Ohms) | C _L Value (pF) |
|---------------------------------|--------------------------------|------------------------------|
| 10TTL | 390 | 15 |
| 5TTL | 780 | 15 |
| 2TTL | 1100 | 6 |
| 10LSTTL | 2000 | 15 |
| 1TTL | 2200 | 3 |







Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth

(>300MHz) passive probe is recommended.

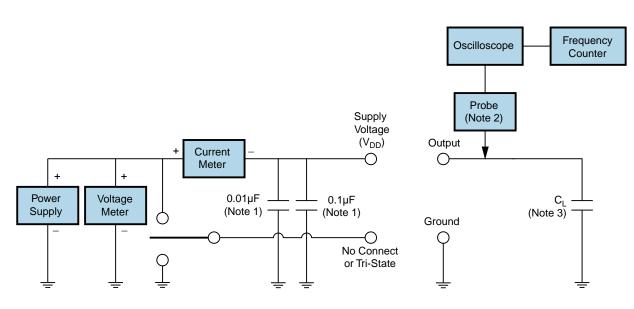
Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



Test Circuit for CMOS Output



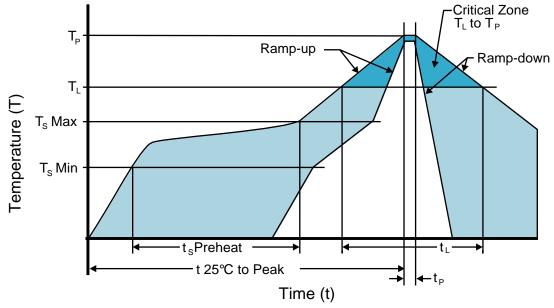
Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_1 includes sum of all probe and fixture capacitance.

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Recommended Solder Reflow Methods



High Temperature Infrared/Convection

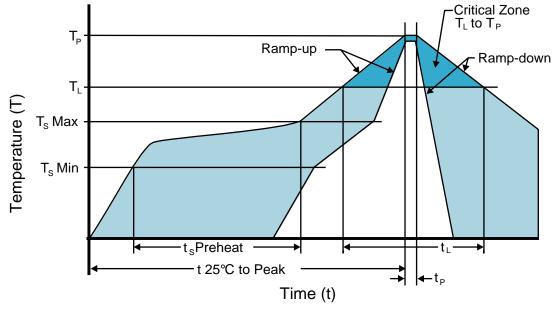
EH2500TS-12.000M

| <u> </u> | |
|---|---|
| T _s MAX to T _L (Ramp-up Rate) | 3°C/second Maximum |
| Preheat | |
| - Temperature Minimum (T _s MIN) | 150°C |
| - Temperature Typical (T _s TYP) | 175°C |
| Temperature Maximum (T_s MAX) | 200°C |
| - Time (t _s MIN) | 60 - 180 Seconds |
| Ramp-up Rate (T⊾ to T _P) | 3°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T∟) | 217°C |
| - Time (t∟) | 60 - 150 Seconds |
| Peak Temperature (T _P) | 260°C Maximum for 10 Seconds Maximum |
| Target Peak Temperature (T _P Target) | 250°C +0/-5°C |
| Time within 5°C of actual peak (t _p) | 20 - 40 seconds |
| Ramp-down Rate | 6°C/second Maximum |
| Time 25°C to Peak Temperature (t) | 8 minutes Maximum |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |
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Recommended Solder Reflow Methods

EH2500TS-12.000M



Low Temperature Infrared/Convection 240°C

| T_s MAX to T_L (Ramp-up Rate) | 5°C/second Maximum |
|--|--|
| Preheat | |
| - Temperature Minimum (T _s MIN) | N/A |
| - Temperature Typical (T _s TYP) | 150°C |
| - Temperature Maximum (T _s MAX) | N/A |
| - Time (t _s MIN) | 60 - 120 Seconds |
| Ramp-up Rate (T⊾ to T _P) | 5°C/second Maximum |
| Time Maintained Above: | |
| - Temperature (T∟) | 150°C |
| - Time (t∟) | 200 Seconds Maximum |
| Peak Temperature (T _P) | 240°C Maximum |
| Target Peak Temperature (T _P Target) | 240°C Maximum 1 Time / 230°C Maximum 2 Times |
| Time within 5°C of actual peak (t _p) | 10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time |
| Ramp-down Rate | 5°C/second Maximum |
| Time 25°C to Peak Temperature (t) | N/A |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)